

FEATURES

- Dual line programmable transient voltage suppressor
- Wide negative firing voltage range: V_{MGL} = -150 V max.
- Low dynamic switching voltages: V_{FP} and V_{DGL}
- Low gate triggering current: I_{GT} = 5 mA max
- Peak pulse current: I_{PP} = 15 A (10/1000 μs)
- Holding current: I_H = 150 mA min

DESCRIPTION

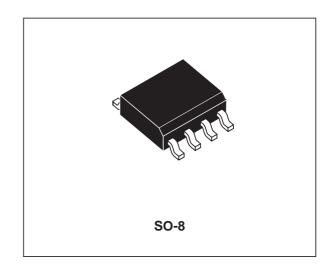
This device has been especially designed to protect 2 new high voltage, as well as classical SLICs, against transient overvoltages.

Positive overvoltages are clamped by 2 diodes. Negative surges are suppressed by 2 thyristors, their breakdown voltage being referenced to $-V_{\text{BAT}}$ through the gate.

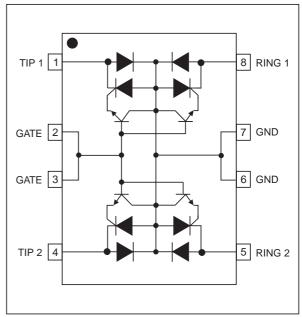
This component presents a very low gate triggering current (I_{GT}) in order to reduce the current consumption on printed circuit board during the firing phase.

BENEFITS

Trisils are not subject to ageing and provide a fail safe mode in short circuit for a better protection. Trisils are used to help equipment to meet various standards such as UL1950, IEC950 / CSA C22.2, UL1459 and FCC part68. Trisils have UL94 V0 resin approved (Trisils are UL497B approved (file: E136224)).



FUNCTIONAL DIAGRAM



LCDP1521

IN COMPLIANCES WITH THE FOLLOWING STANDARDS

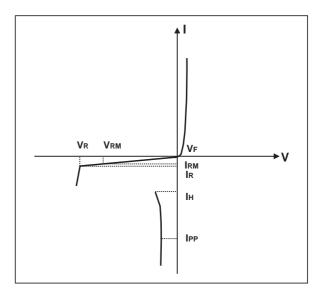
STANDARD	Peak Surge Voltage (V)	Voltage Waveform	Required peak current (A)	Current Waveform	$\begin{array}{l} \mbox{Minimum serial} \\ \mbox{resistor to meet} \\ \mbox{standard} \left(\Omega \right) \end{array}$
GR-1089 Core First level	2500 1000	2/10µs 10/1000µs	500 100	2/10µs 10/1000µs	31 57
GR-1089 Core Second level	5000	2/10µs	500	2/10µs	62
GR-1089 Core Intra-building	1500	2/10µs	100	2/10µs	7
ITU-T-K20/K21	6000 1500	10/700µs	150 37.5	5/310µs	200 20
ITU-T-K20 (IEC61000-4-2)	8000 15000	1/60 ns	ESD contact ESD air di		0 0
VDE0433	4000 2000	10/700µs	100 50	5/310µs	120 40
VDE0878	4000 2000	1.2/50µs	100 50	1/20µs	27 0
IEC61000-4-5	4000 4000	10/700µs 1.2/50µs	100 100	5/310µs 8/20µs	120 27
FCC Part 68, lightning surge type A	1500 800	10/160µs 10/560µs	200 100	10/160µs 10/560µs	43 32
FCC Part 68, lightning surge type B	1000	9/720µs	25	5/320µs	0

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
Rth (j-a)	Junction to ambient	170	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C)

Symbol	Parameter
I _{GT}	Gate triggering current
Iн	Holding current
I _{RM}	Reverse leakage current LINE / GND
I _{RG}	Reverse leakage current GATE / LINE
V _{RM}	Reverse voltage LINE / GND
V _{GT}	Gate triggering voltage
VF	Forward drop voltage LINE / GND
V _{FP}	Peak forward voltage LINE / GND
V _{DGL}	Dynamic switching voltage GATE / LINE
VGATE	GATE / GND voltage
V _{RG}	Reverse voltage GATE / LINE
С	Capacitance LINE / GND

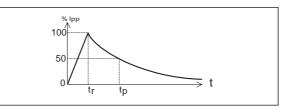


Symbol	Parameter		Value	Unit
Ipp	Peak pulse current (see note1)	10/1000μs 8/20μs 10/560μs 5/310μs 10/160μs 1/20μs 2/10μs	15 60 20 25 30 60 70	A
ITSM	Non repetitive surge peak on-state current (50Hz sinusoidal)	t = 10ms t = 1s	5 3.5	A
l ² t	l ^² t value for fusing (50Hz sinusoidal)	t = 10ms	0.125	A ² s
I _{GSM}	Maximum gate current (50Hz sinusoidal)	t = 10ms	2	A
V _{MLG} V _{MGL}	Maximum voltage LINE/GND Maximum voltage GATE/LINE	-40°C < Tamb < +85°C -40°C < Tamb < +85°C	-150 -150	V
T _{stg} Tj	Storage temperature range Maximum junction temperature	- 55 to + 150 150	°C	
TL	Maximum lead temperature for solde	ring during 10s	260	°C

ABSOLUTE RATINGS (T_{amb} = 25°C, unless otherwise specified).

Repetitive peak pulse current

tr: rise time (μ s) tp: pulse duration (μ s) ex: Pulse waveform 10/1000 μ s tr = 10 μ s tp = 1000 μ s



PARAMETERS RELATED TO THE DIODE LINE / GND $(T_{amb}$ = 25 $^{\circ}C)$

Symbol		Мах	Unit			
VF	I _F = 1A		t =	500µs	2	V
V _{FP} (note 1)	10/700μs 1.2/50μs 2/10μs	1.5kV 1.5kV 2.5kV	$R_{s} = 110\Omega$ $R_{s} = 60\Omega$ $R_{s} = 245\Omega$	$I_{PP} = 10A$ $I_{PP} = 15A$ $I_{PP} = 10A$	5 10 20	V

Note 1: see test circuit for VFP; RS is the protection resistor located on the line card.

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PARAMETERS RELATED TO THE PROTECTION THYRISTOR (T_{amb} = 25°C unless otherwise specified)

Symbol	Test conditions	Min	Max	Unit	
I _{GT}	$V_{\text{gND/LINE}} = -48V$	0.1	5	mA	
Iн	$V_{GATE} = -48V$ (note 2)	150		mA	
V _{GT}	at I _{st}		2.5	V	
I _{RG}	V _{RG} = -150V V _{RG} = -150V	Tc=25°C Tc=85°C		5 50	μA
V _{DGL}	V _{GATE} = -48V (note 3)				
	$\begin{array}{ccc} 10/700 \mu s & 1.5 kV & R_s = 110 \Omega \\ 1.2/50 \mu s & 1.5 kV & R_s = 60 \Omega \\ 2/10 \mu s & 2.5 kV & R_s = 245 \Omega \end{array}$	$I_{_{\rm PP}} = 10A$ $I_{_{\rm PP}} = 15A$ $I_{_{\rm PP}} = 10A$		5 10 20	V

Note 2: see functional holding current (IH) test circuit

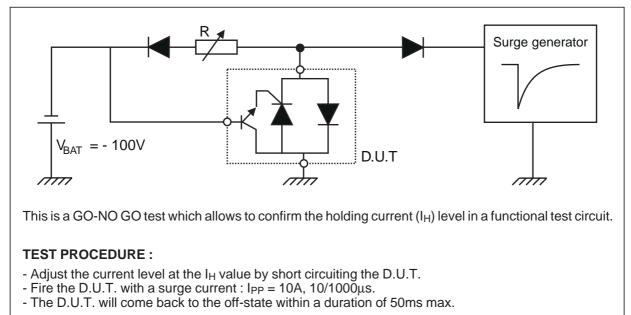
Note 3: see test circuit for VDGL

The oscillations with a time duration lower than 50ns are not taken into account

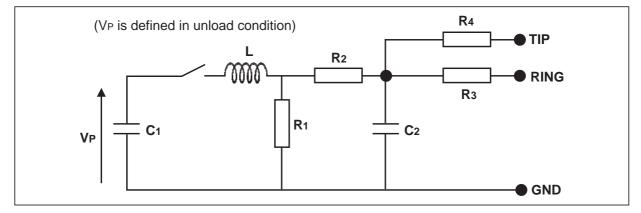
PARAMETERS RELATED TO DIODE AND PROTECTION THYRISTOR (T_{amb} = 25°C, unless otherwise specified)

Symbol	Test conditions	Тур.	Max.	Unit	
I _{RM}	$\begin{array}{l} V_{\text{gate / Line}} = -1V & V_{\text{RM}} = -150V \\ V_{\text{gate / Line}} = -1V & V_{\text{RM}} = -150V \end{array}$	Tc=25°C Tc=85°C		5 50	μΑ
С	$V_{R} = 50V$ bias, $V_{RMS} = 1V$, F = 1MHz $V_{R} = 2V$ bias, $V_{RMS} = 1V$, F = 1MHz		20 48		pF

FUNCTIONAL HOLDING CURRENT (I_H) TEST CIRCUIT : GO-NO GO TEST



TEST CIRCUIT FOR V_{FP} AND V_{DGL} PARAMETERS



Pulse	e (µs)	Vp	C ₁	C ₂	L	R ₁	R ₂	R ₃	R4	IPP	Rs
tr	tp	(V)	(μF)	(nF)	(µH)	(Ω)	(Ω)	(Ω)	(Ω)	(A)	(Ω)
10	700	1500	20	200	0	50	15	25	25	10	110
1.2	50	1500	1	33	0	76	13	25	25	15	60
2	10	2500	10	0	1.1	1.3	0	3	3	10	245

TECHNICAL INFORMATION

Fig. A1: LCDP1521 concept behavior.

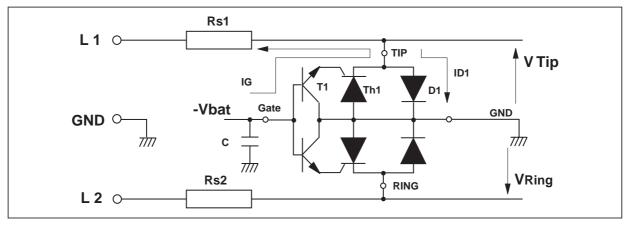


Figure A1 shows the classical protection circuit using the LCDP1521 crowbar concept. This topology has been developed to protect the new high voltage SLICs. It allows to program the negative firing threshold while the positive clamping value is fixed at GND.

When a negative surge occurs on one wire (L1 for example), a current IG flows through the base of the transistor T1 and then injects a current in the gate of the thyristor Th1. Th1 fires and all the surge current flows through the ground. After the surge when the current flowing through Th1 becomes less negative than the holding current I_H , then Th1 switches off.

When a positive surge occurs on one wire (L1 for example), the diode D1 conducts and the surge current flows through the ground.

The capacitor C is used to speed up the crowbar structure firing during the fast surge edges.

This allows to minimize the dynamical breakover voltage at the SLIC Tip and Ring inputs during fast strikes. Note that this capacitor is generally present around the SLIC - Vbat pin.

So to be efficient it has to be as close as possible from the LCDP1521 Gate pin and from the reference ground track (or plan). The optimized value for C is 220nF.

The series resitors Rs1 and Rs2 designed in figure A1 represent the fuse resistors or the PTC which are mandatory to withstand the power contact or the power induction tests imposed by the various country standards. Taking into account this fact the actual lightning surge current flowing through the LCDP is equal to:

I surge = V surge / (Rg + Rs)

With V surge = peak surge voltage imposed by the standard.

Rg = series resistor of the surge generator

Rs = series resistor of the line card (equivalent to PTC + R on Fig. A2)

e.g. For a line card with 60Ω of series resistors which has to be qualified under GR1089 Core 1000V 10/1000µs surge, the actual current through the LCDP1521 is equal to:

The LCDP1521 is particularly optimized for the new telecom applications such as the fiber in the loop, the WLL, the remote central office. In this case, the operating voltages are smaller than in the classical system. This makes the high voltage SLICs particularly suitable. The schematics of figure A2 gives the most frequent topology used for these applications.



Fig. A2: Protection of high voltage SLICs.

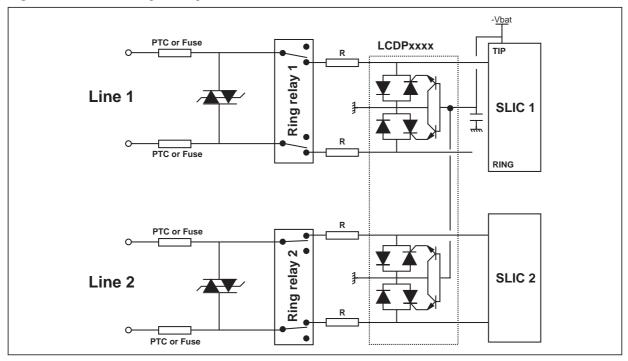
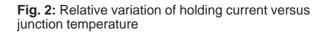
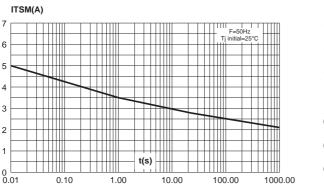
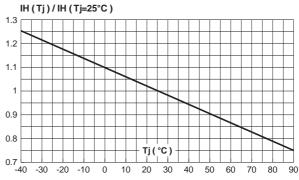


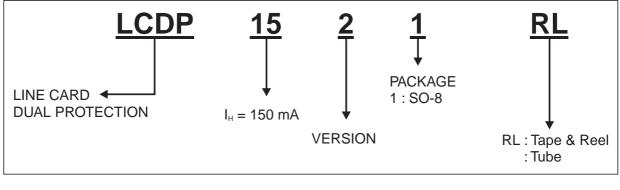
Fig. 1: Surge peak current versus overload duration.





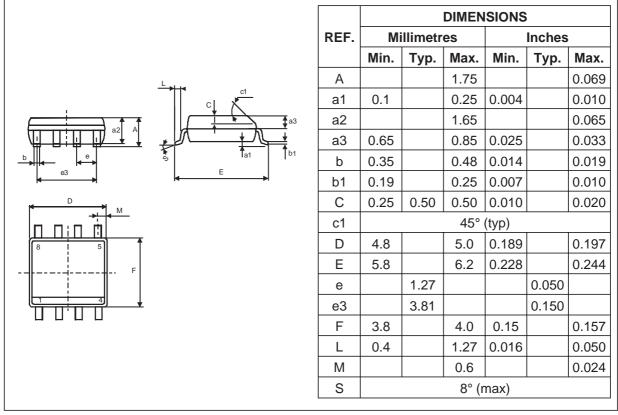


ORDER CODE



PACKAGE MECHANICAL DATA

SO-8 (Plastic)



Order code	Marking	Package	Weight	Base qty	Delivery mode
LCDP1521	CDP152	SO-8	0.08 g	100	Tube
LCDP1521RL	CDP152	SO-8	0.08 g	2500	Tape & Reel

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